

ABSTRACT AMENDMENTS

Replace the Abstract with:

~~The invention provides a~~ A semiconductor device having ~~stability in stable~~ device characteristics, in which variation in contact resistance between silicon and poly-silicon or between poly-silicon and poly-silicon is reduced. ~~The invention also provides a method of manufacturing the semiconductor device.~~ In the a cleaning process before forming an upper layer poly-silicon film 11, ~~an H₂O₂~~ a treatment is conducted to form a thin uniform oxide film 20 of about 0.5nm to 10nm in thickness (to the extent of permitting an impurity to diffuse through the film) on the surface of silicon. After forming the upper layer poly-silicon film 11, a removed portion is uniformly formed on the thin uniform oxide film by applying a short time, high temperature annealing treatment ~~by RTP (Rapid Thermal Process).~~